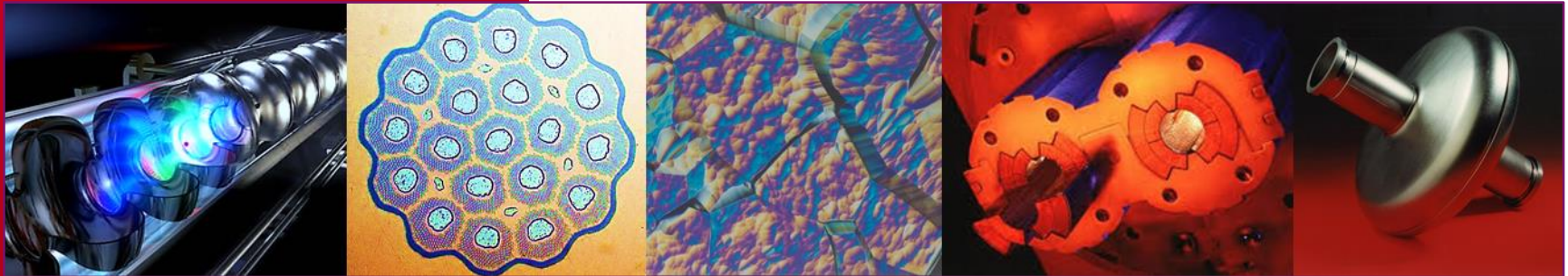


DE LA RECHERCHE À L'INDUSTRIE



# STATUS AND EXPECTED PROGRESS ON SRF CAVITIES



| *Réunion d'information ILC -9avril 2018*

**INTRODUCTION**

**SRF LIMITS**

## Niobium cavities

### ■ Performances

- $E_{acc} \propto H_{RF}$
- $Q_0 (\propto 1/R_s) \propto T_C \Rightarrow \text{Nb}_3\text{Sn}, \text{MgB}_2, \text{NbN}...$
- Limit = magnetic transition of the SC material @  $H_{peak}$

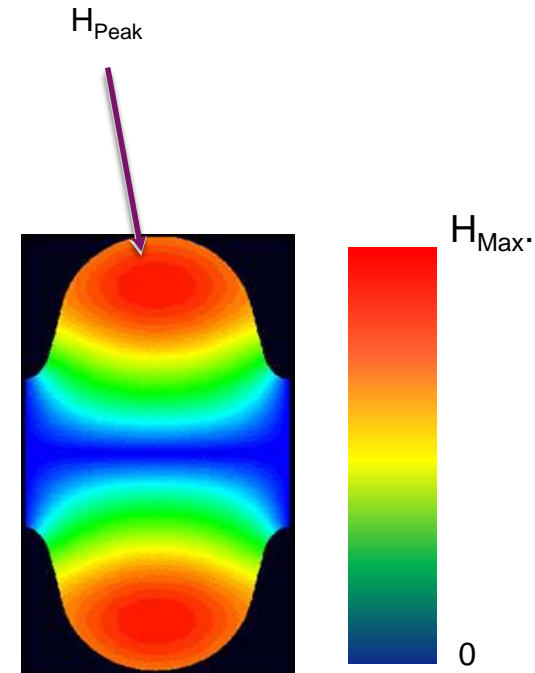
### ■ Superconductivity only needed inside :

- Thickness  $\sim < 1 \mu\text{m} \Rightarrow$  thin films
- (onto a thermally conductive, mechanically resistant material, e.g. Cu)

### ■ Today :

- Thin films exhibit too many defects
- Only Bulk Nb has high SRF performances

### ■ Issues : getting “defect free” superconductors (yes but not all defects are detrimental...)



H field mapping in an elliptical cavity

## ■ SC phase diagram

■ All SC applications except SRF:

**mixed state** w. vortex

- Vortices dissipate in RF !

■ SRF => Meissner state **mandatory !**

■  $H_{C1}$  = limit Meissner/mixed state

■ Nb: highest  $H_{C1}$  (180 mT)

■ “Superheating field”(?) :

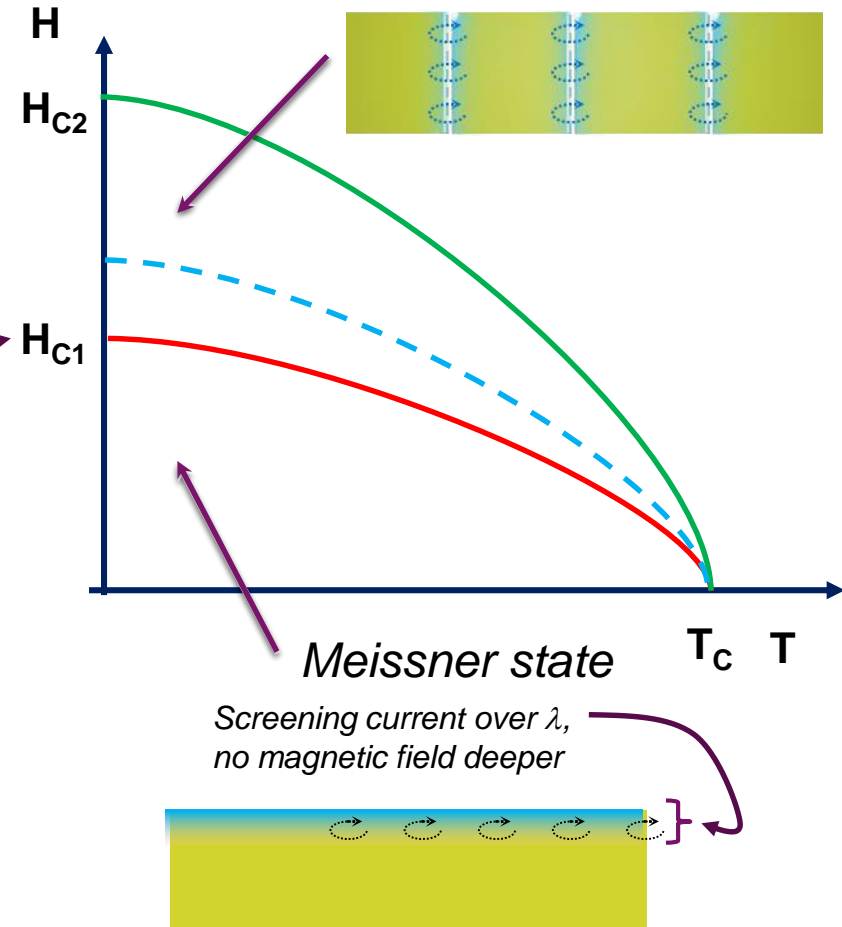
**Metastable state favored**



**by  $H //$  to surface**

- Difficult to get in real life !

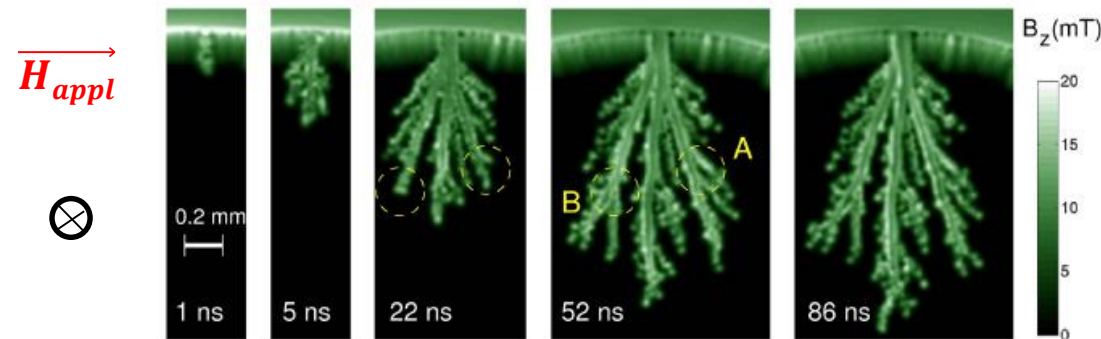
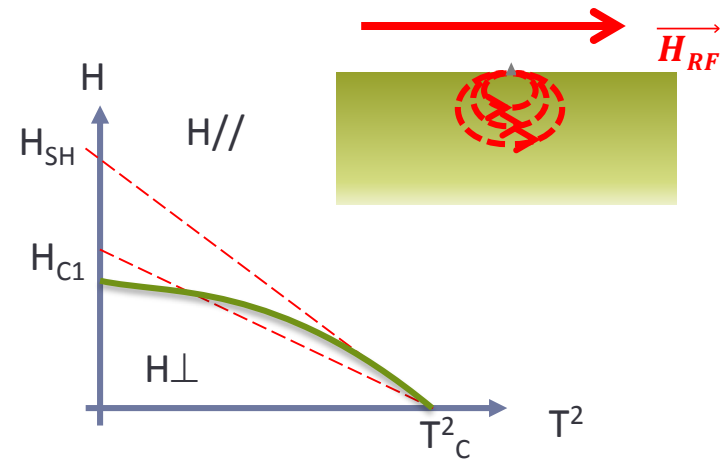
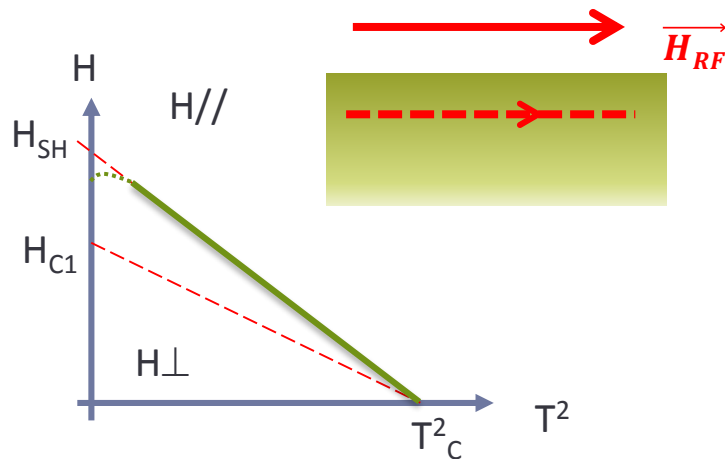
*Mixed state w. Vortex*  
(i.e. N. cond. flux line + screening currents)



# WHAT IS THE LIMIT ( $H_P/H_{C1}/H_{SH}$ ) ?

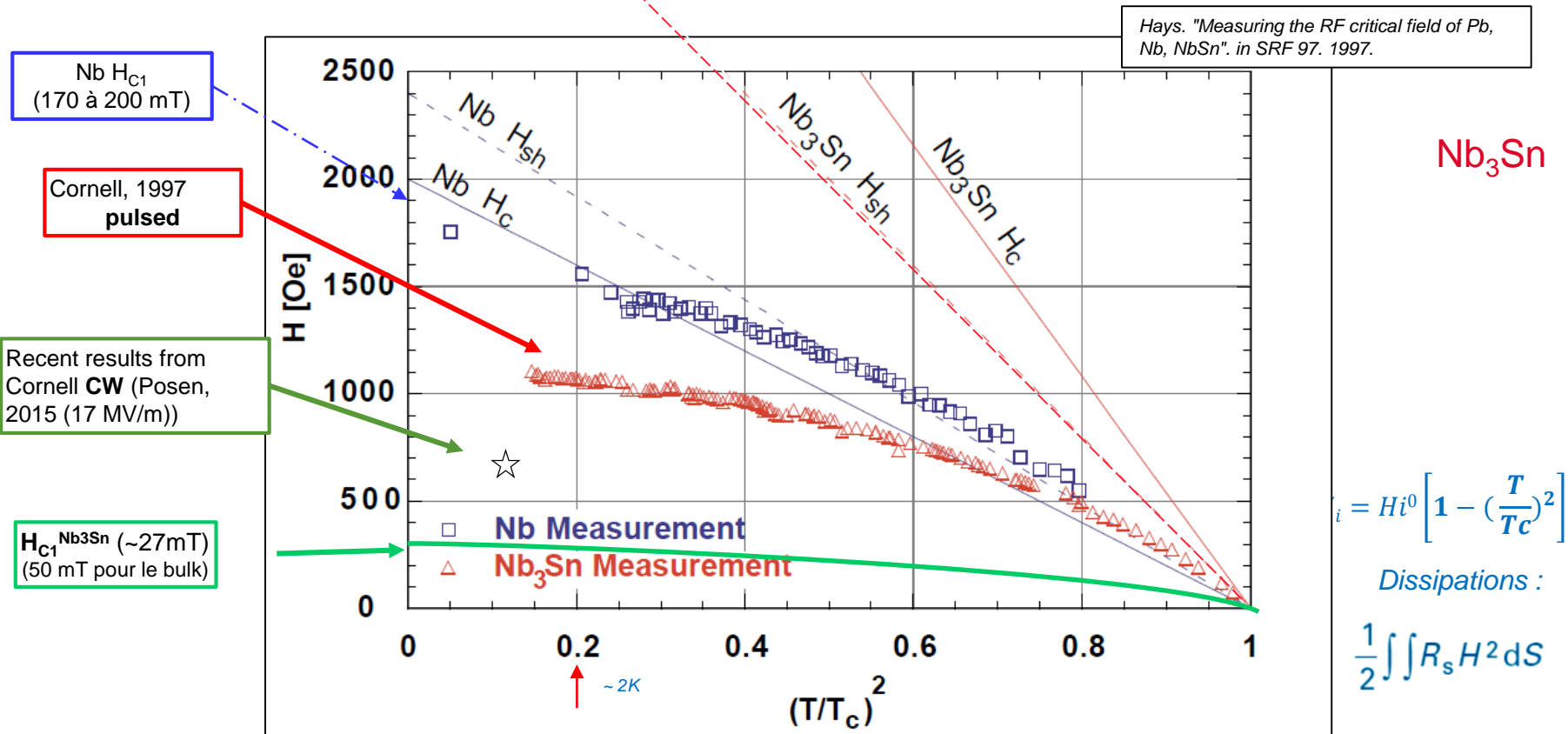


- Real world cavities behavior is dominated by a few number of defects
- It is very important to measure the penetration field of samples in realistic conditions



- $\sim 100 \mu\text{m}$  in 1 ns ( $\sim$ RF period)
- Compare with  $\lambda$  (field penetration depth)
  - Nb :  $\sim 40 \text{ nm}$
  - MgB<sub>2</sub>  $\sim 200 \text{ nm}$
- Avalanche : high RF dissipation

MgB<sub>2</sub>:  
[http://www.nature.com/srep/2012/121126/srep00886/full/srep00886.html?message-global=remove&WT.ec\\_id=SREP-20121127](http://www.nature.com/srep/2012/121126/srep00886/full/srep00886.html?message-global=remove&WT.ec_id=SREP-20121127)



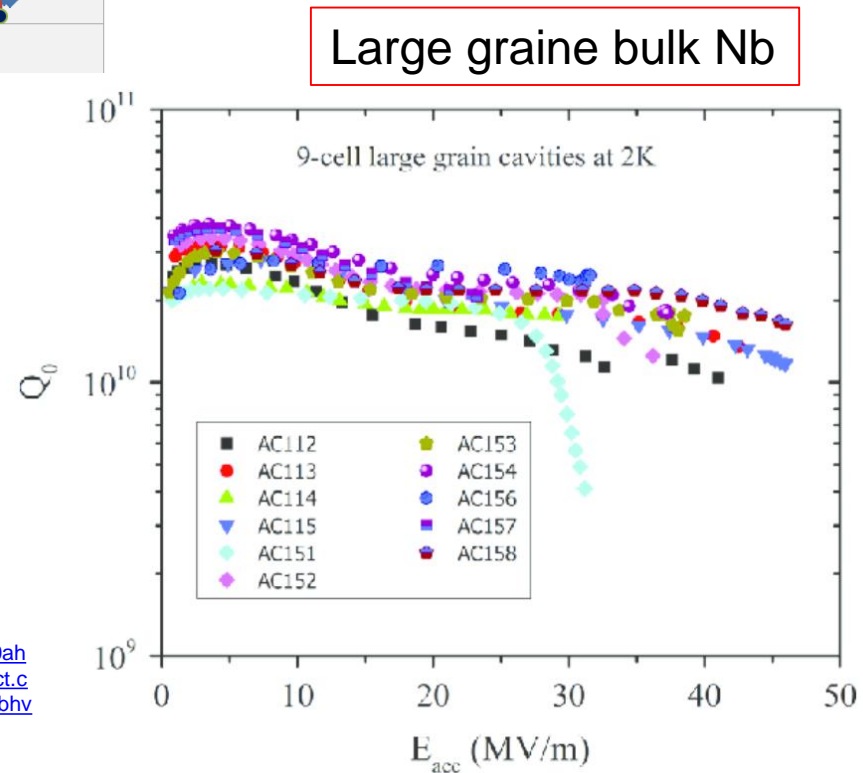
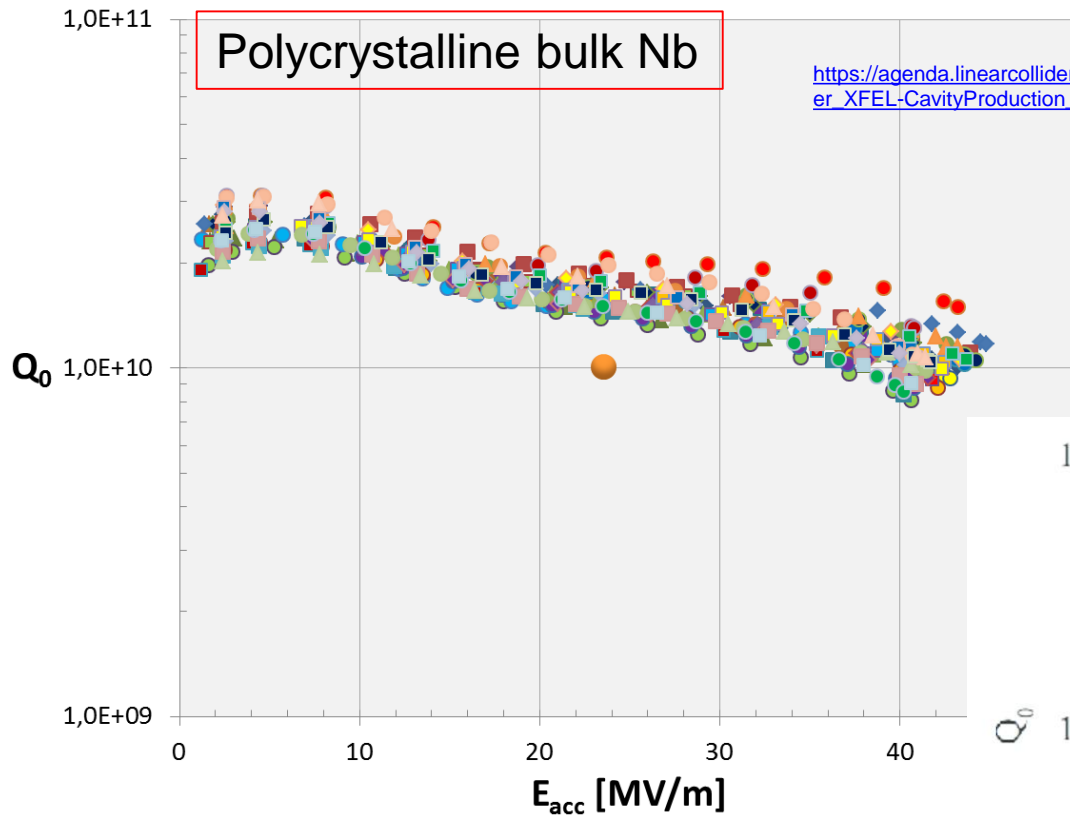
## ■ Vortices enter more easily at lower temperature (counter intuitive !)?

- @  $T \sim T_c$  :  $H$  is low => low dissipations => easy to thermally stabilize
- @  $T \ll T_c$  :  $H$  is high => even if small defect => high dissipations => Favors flux jumps

=> We have to reduce defect density (yes but which ones?)

**BULK NIOBIUM**

**PRESENT STATUS**



[https://www.google.fr/url?sa=t&rct=j&q=&esrc=s&source=web&cd=1&cad=rja&uact=8&ved=0ahUKewjH57Di8qzaAhULuRQKHbUeBh4QFggsMAA&url=https%3A%2F%2Fwww.sciencedirect.com%2Fscience%2Farticle%2Fpii%2FS0168900214013977&usq=AOvVaw2\\_X7xJ6spZFAA0bhvMpxf](https://www.google.fr/url?sa=t&rct=j&q=&esrc=s&source=web&cd=1&cad=rja&uact=8&ved=0ahUKewjH57Di8qzaAhULuRQKHbUeBh4QFggsMAA&url=https%3A%2F%2Fwww.sciencedirect.com%2Fscience%2Farticle%2Fpii%2FS0168900214013977&usq=AOvVaw2_X7xJ6spZFAA0bhvMpxf)

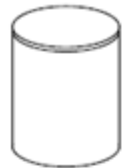


## Many trails explored...

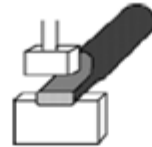
- **Large grain material**
  - Economy in Nb Weight
- **Nitrogen (Oxygen ?) doping/infusion**
  - Today Nb is optimized for thermal conduction (stabilization), not for superconductivity
  - Modification of the surface without losing the bulk properties
- **Multilayer :**
  - Route to realistic material with higher  $Q_0$  and  $E_{acc}$  (and even defects)
  - Protection against vortex avalanche
- **Getting rid of the damage layer**
  - Only explored at lab level

**LARGE GRAIN MATERIAL**

# TYPICAL SHEET PREPARATION



Mother material



Forging



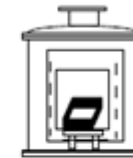
Cutting



Pressing



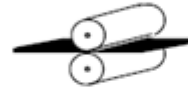
Milling



Annealing



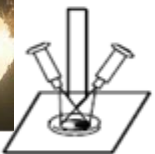
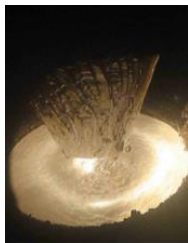
1st EB melting



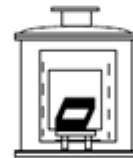
Rolling



Leveling



2nd, 3rd etc. EB melting



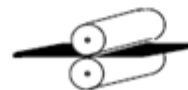
Annealing



Polishing



Separate from base plate



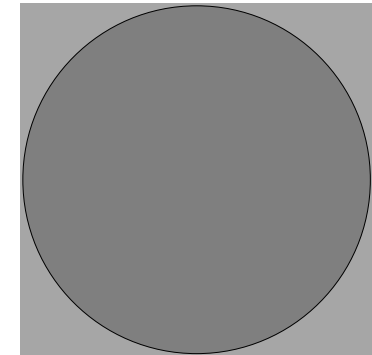
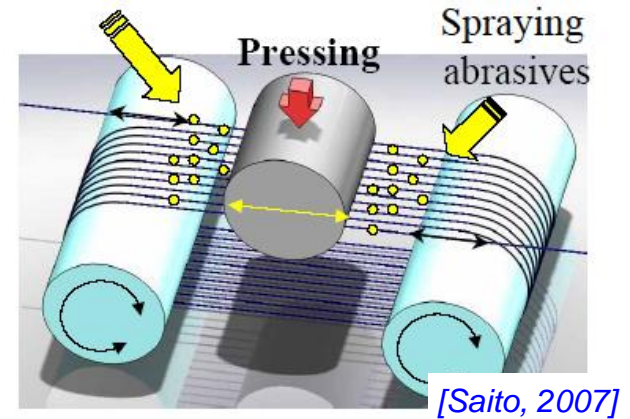
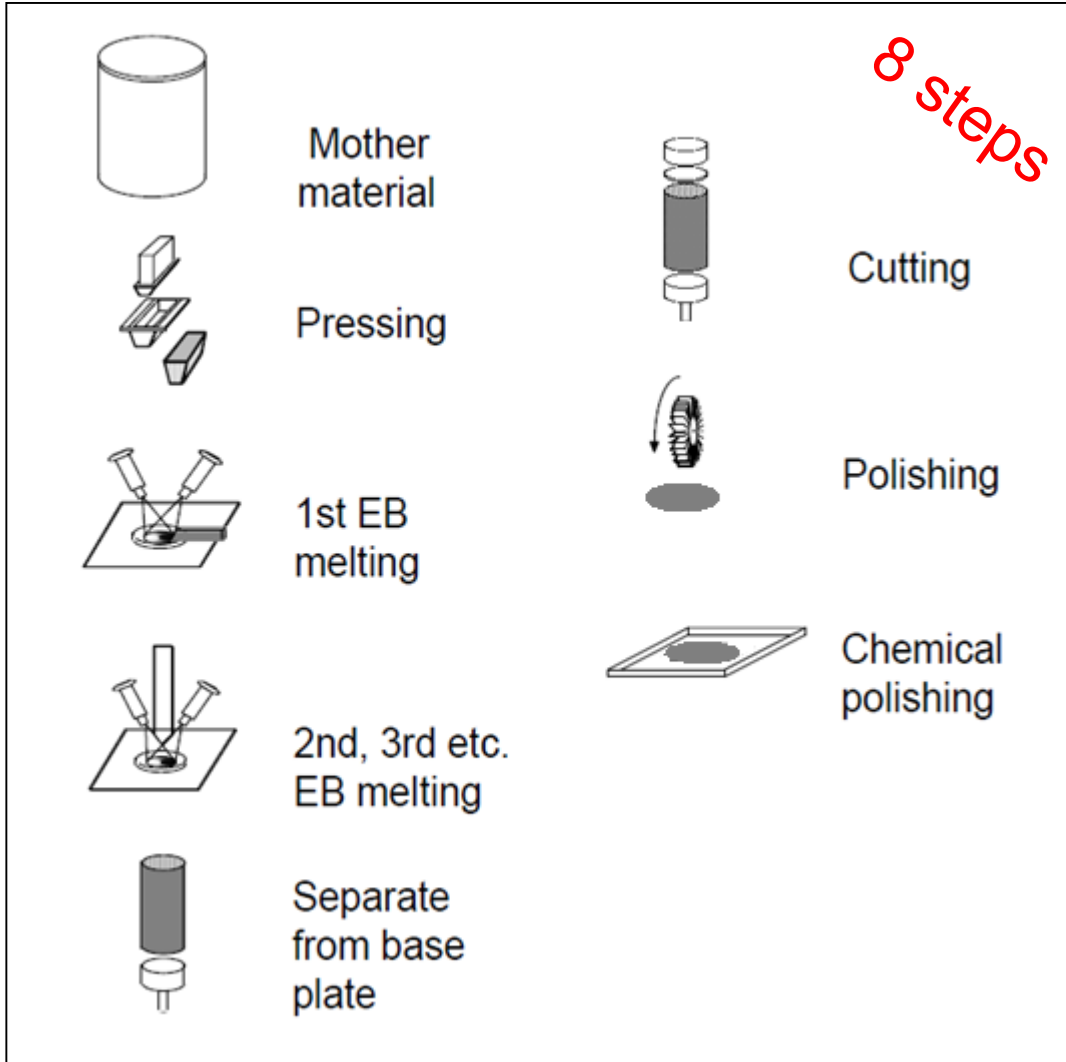
Rolling

(2 or 3 times)



Chemical polishing

15-20 steps

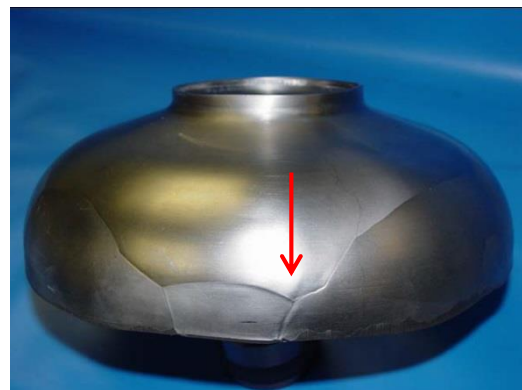


- Economy in weight:
  - ≠ ~ 6 Kg/ 9-cell
  - ~ 3 k€ / 9-cell (compare w. 20 k€)
  - ~ 15% of the cost

But....



- Non uniform forming
  - asymmetric deformation
  - risk of tearing (irises)
  - risk of holes during welding
  - larges steps @ GB



Light microscope image of LGs sample after 100  $\mu\text{m}$  BCP

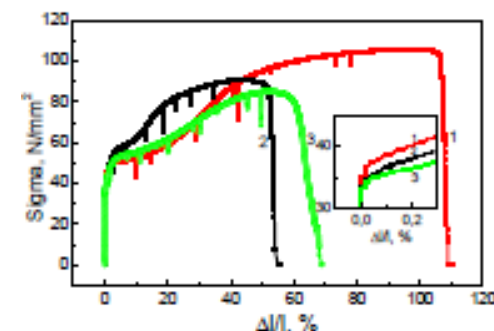
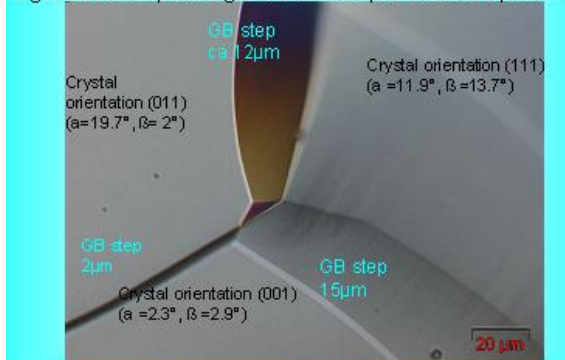


Figure 5. Elongation tests results for 3 single crystal samples with different orientations.

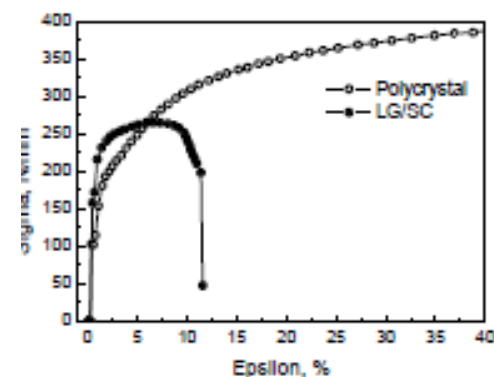


Figure 7. Biaxial bulging test results on large strain Nb sample. Curve for polycrystalline

[Singer, 2008]

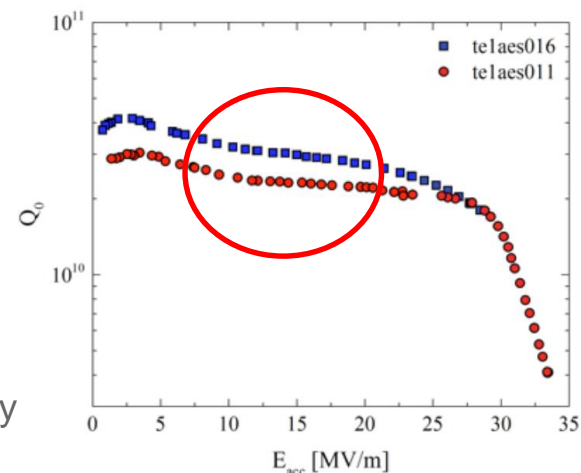
=> a lot of forming failure

=> a whole new industrial process need to be developed

- RF performances : ~ same as smaller grain cavities
  - Medium Q ~ a little better for EP cavities
- Savings for (very) large Nb sheet production (small elliptical cavities only)
  - Less fabrication steps
  - Ingot => disks : no losses of material in the corners
  - High purity material with intrinsically good crystalline quality

But not fitted for  $\varnothing > 30$  cm (typical ingot  $\varnothing$ )

- Increased costs and delay for Cavity forming
  - More fabrication steps, higher failure risks



Large cost savings on material, ...might be lost on fabrication

**NITROGEN (OXYGEN ?)**

**DOPING/INFUSION**

# BAKING/DOPING/INFUSION WHAT IS THE DIFFERENCE?



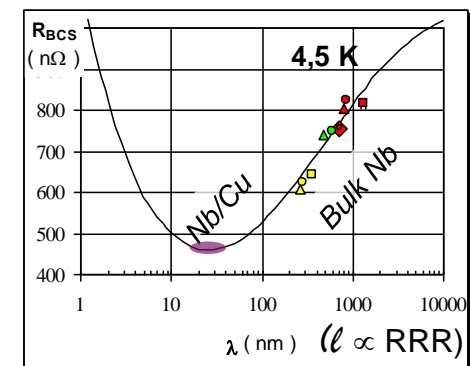
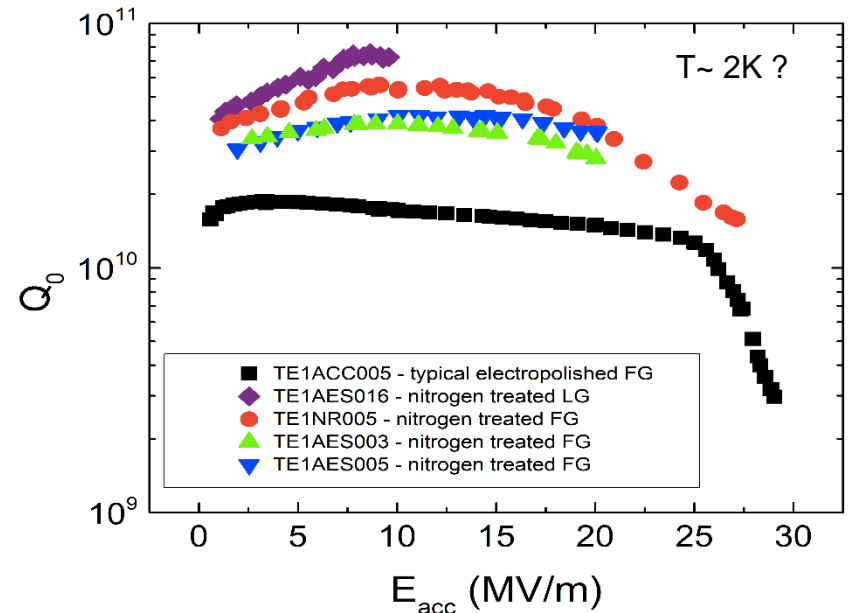
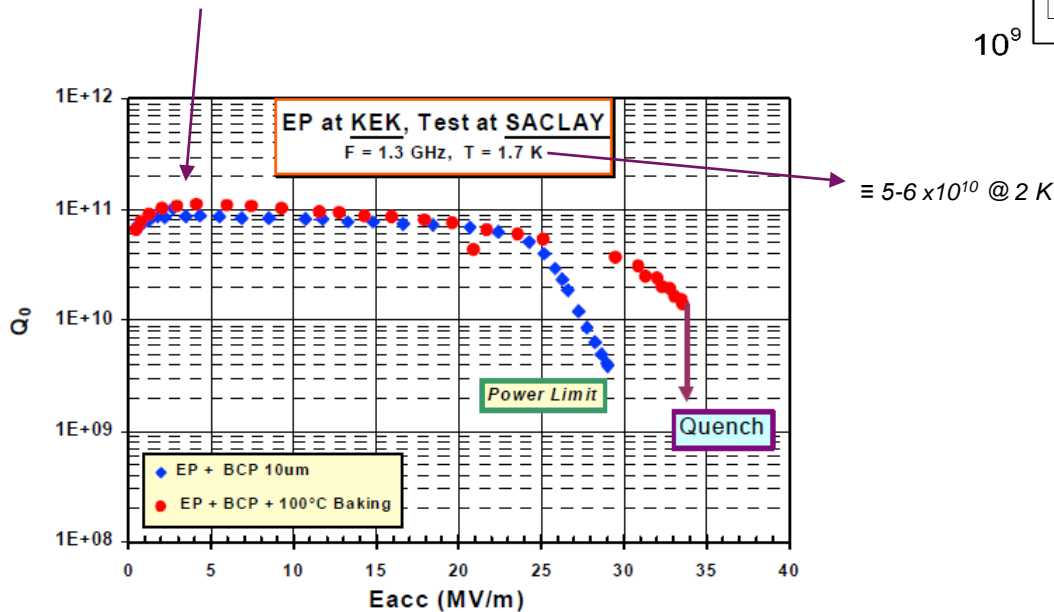
## N doping

- high temperature annealing (oxide disappears)
- high temperature  $N_2 \Rightarrow$  degradation
- EP ( $\sim 80 \mu m$ )  $\Rightarrow$  very high  $Q_0$ , but  $E_{acc} \downarrow \downarrow$
- At 1<sup>st</sup> order : modification of *m.f.p.*  $\ell$

## Not For ILC !!!

- Not necessarily related to N
- Very well recrystallized material

@ Saclay in 2001



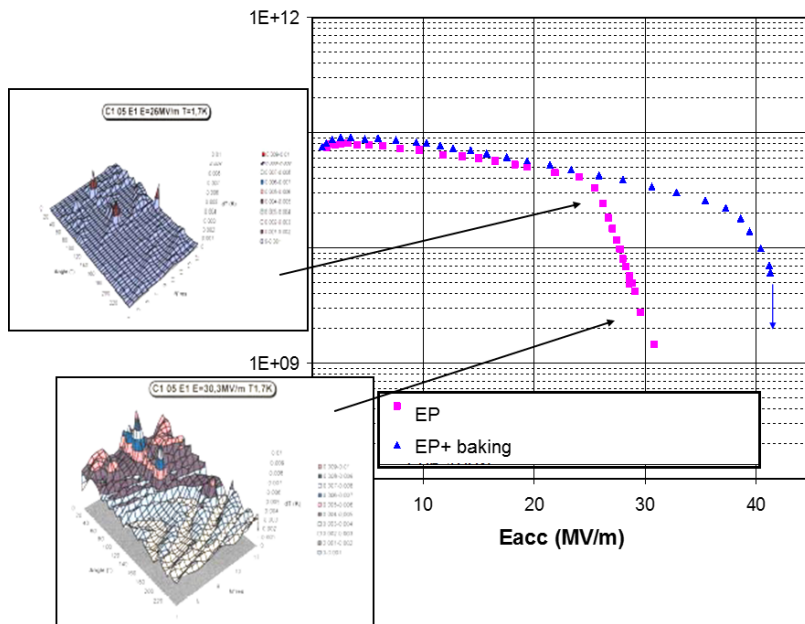


# BAKING/DOPING/INFUSION WHAT IS THE DIFFERENCE?



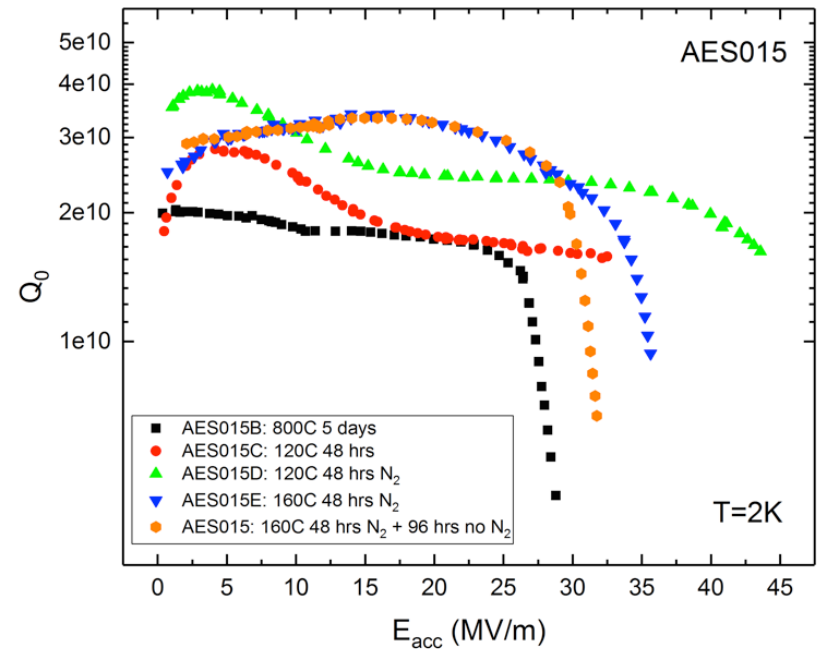
## Baking

- 120 °C, 48 h => oxide degrades,  $O_i$  diffuses ~100 nm
- Change in mean free path => better  $R_S$
- prevents hydride precipitation ?



## N infusion

- 800°C annealing (oxide disappears)
- 120 °C, 48 h in presence of  $N_2$  =>  $N_i$  diffuses ~10 nm
- Change in mean free path => better  $R_S$
- prevents hydride precipitation ?

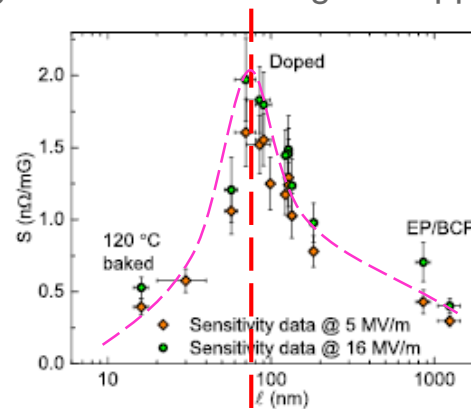


## Variability lab to lab

- Same recipe, but not same results,
- Needs adaptation : high temperature treatment  $\neq$

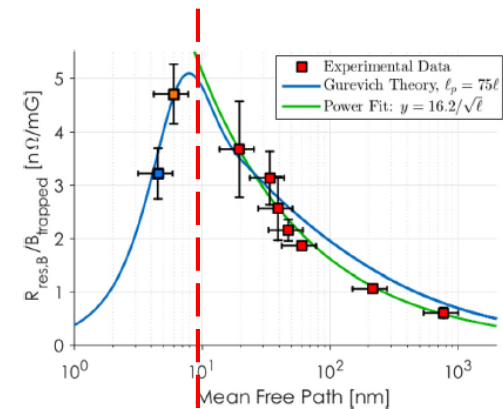
## Higher sensitivity to trap flux

- Upon cooldown if  $\exists$  defects, magnetic remnant flux gets trapped
- very high surf resistance in RF !



$\sim 100 \text{ nm} \Rightarrow$   
*dislocation cells*

*Martinello et al, FNAL*



$\sim 10 \text{ nm} \Rightarrow$   
*interstitials*

*Gonella et al, CORNELL U.*

Related to crystalline sub-structure, not  
specified/monitored yet

# MULTILAYERS



Structures proposed by A. Gurevich in 2006, SRF tailored

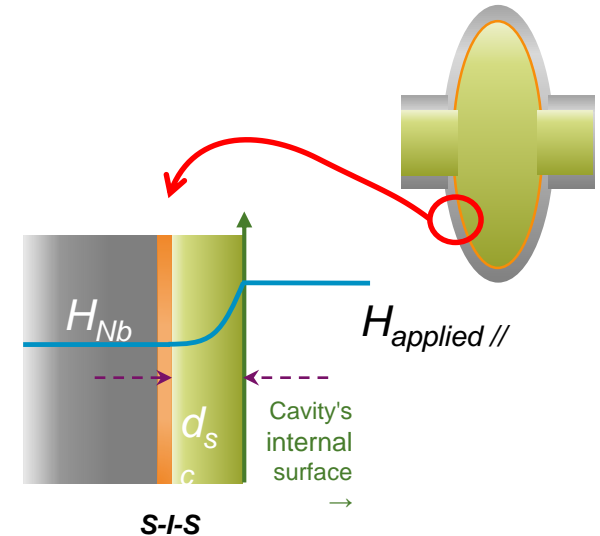
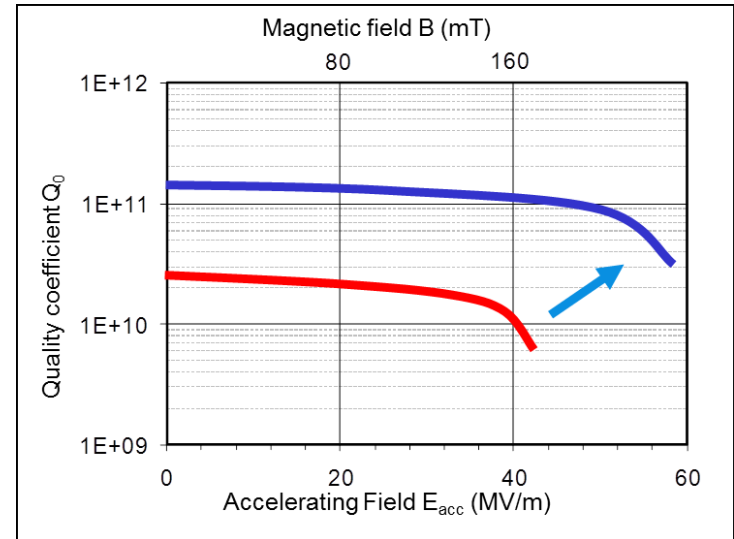
## ■ Dielectric layer

- Small  $\perp$  vortex (short  $\rightarrow$  low dissipation)
  - Quickly coalesce (w. RF)
  - Blocks avalanche penetration
- $\Rightarrow$  **Multilayer** concept for RF application

## ■ Nanometric I/S// layers deposited on Nb

- SC nanometric layers ( $\leq 100$  nm)  $\Rightarrow H_{C1} \uparrow \Rightarrow$  Vortex enter at higher field
- Nb surface screening  $\Rightarrow$  allows high magnetic field inside the cavity  $\Rightarrow$  higher  $E_{acc}$

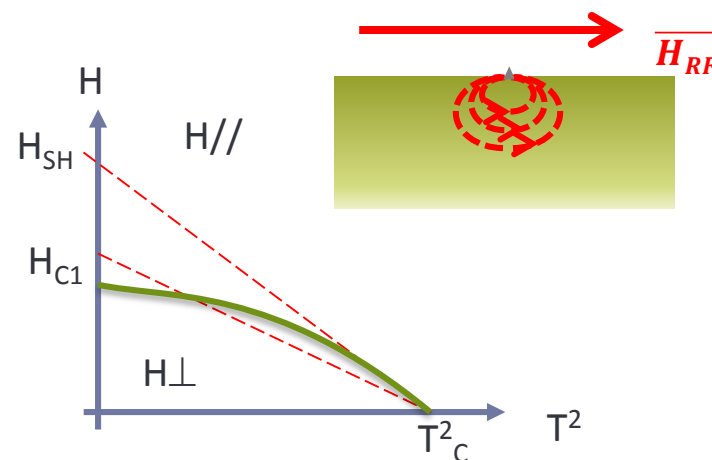
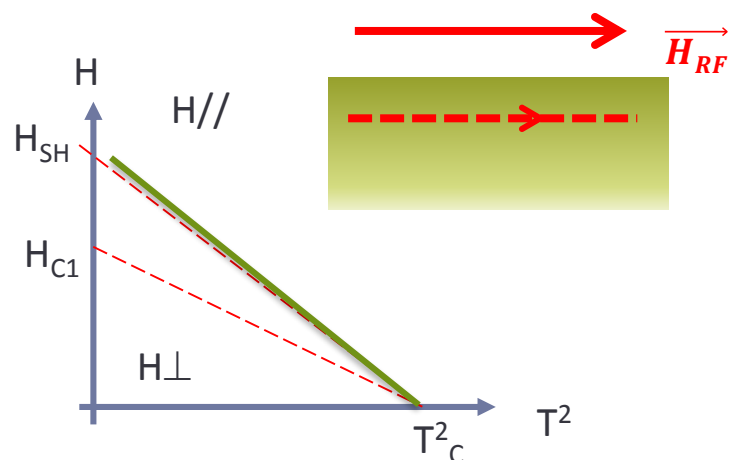
- SC w. high  $T_C$  than Nb (e.g. NbN):  $R_s^{NbN} \approx \frac{1}{10} R_s^{Nb}$
- $\Rightarrow Q_0^{multi} \gg Q_0^{Nb}$



# WHAT IS THE LIMIT ( $H_P/H_{C1}/H_{SH}$ ) ?

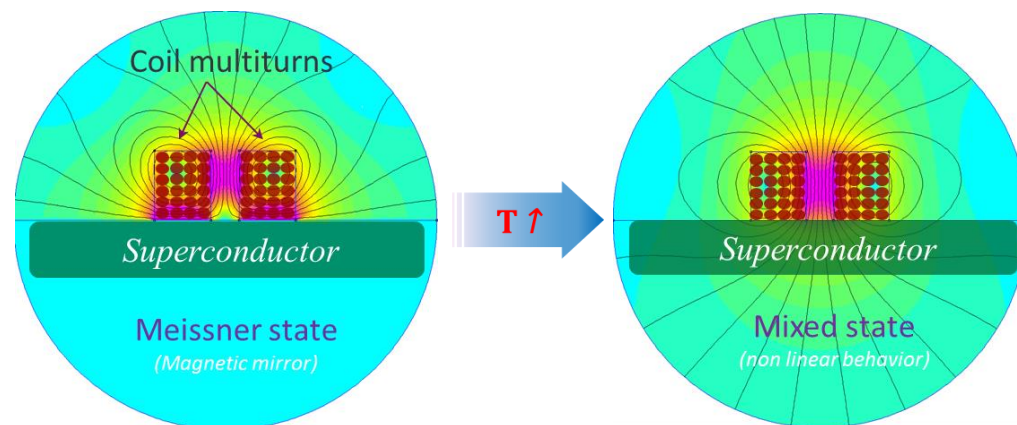


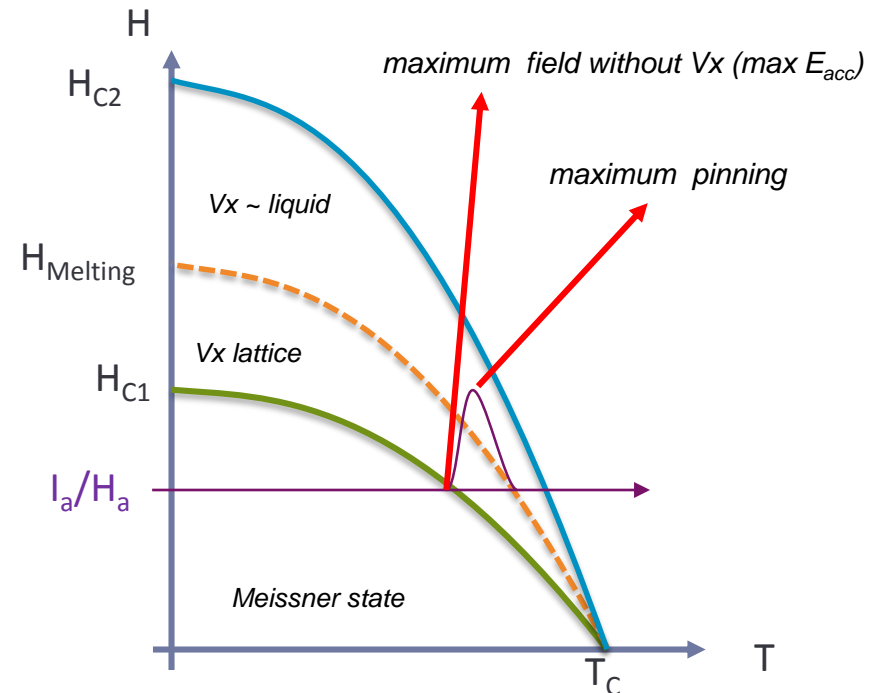
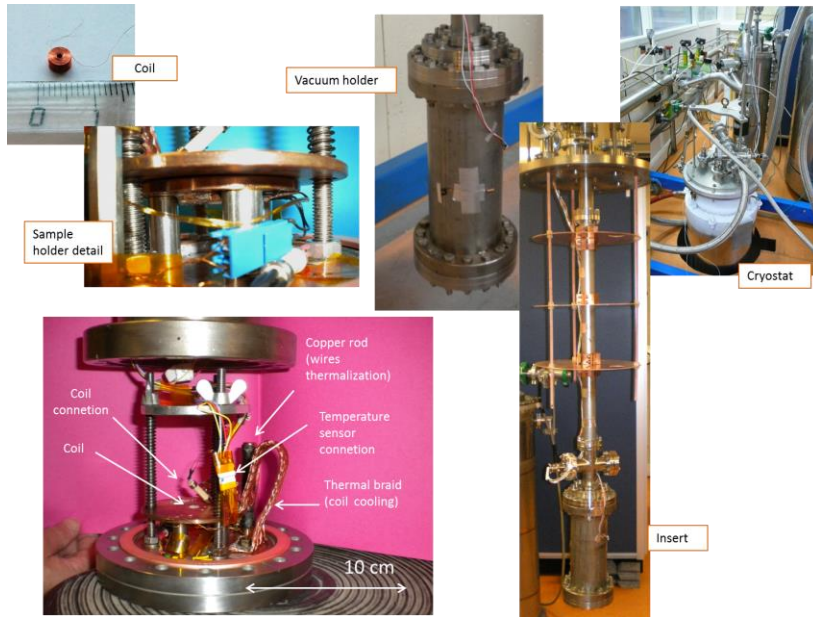
- Real world cavities behavior is dominated by a few number of defects
- It is very important to measure the penetration field of samples in realistic conditions



## Local magnetometry

- ~ Same geometry as cavities
- No shape/edge effect (vs DC/ Squid magnetometry)
- No demagnetization effect
- Measures actual penetration field wherever it is  $H_P/H_{C1}/H_{SH}$

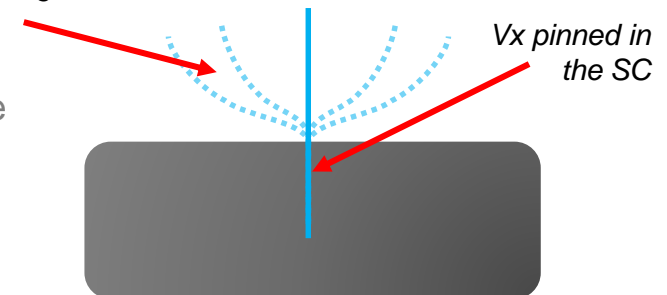




## Low frequency $\equiv$ DC :

- $0 < H_a < H_{C1} \Rightarrow R=0$ , Meissner state
- $H_{C1} < H_a < H_M \Rightarrow V_x$  are trapped,  $R=0$ , Campbell regime
- $H_M < H_a < H_{C2} \Rightarrow V_x$  are moving liquid like,  $R \neq 0$ , Flux flow regime
- Third harmonic signal arise from flux line tension (affects the e- inside the Cu coil),
- It does not depend on dissipation inside Nb, BUT depends on # of  $V_x$  trapped there (and length).

flux line moving in AC field



## NbN coating by Magnetron Sputtering

### NbN single layers series

- NbN SL / “thick” Nb layer
  - Magnetron sputtered
  - MgO as dielectric layer
- Far from perfect...



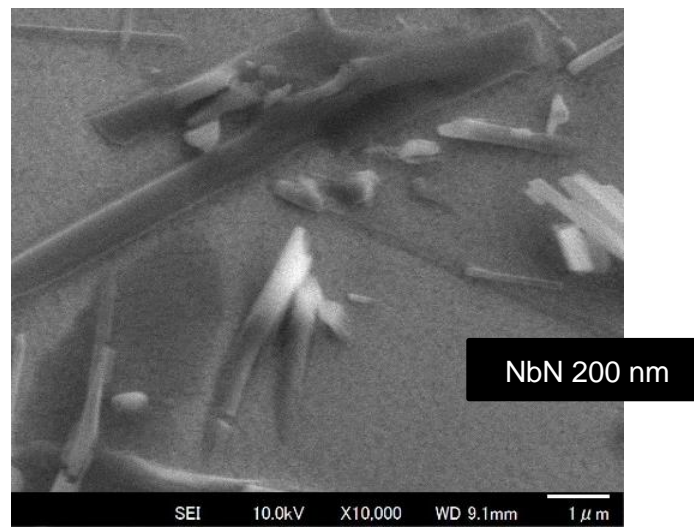
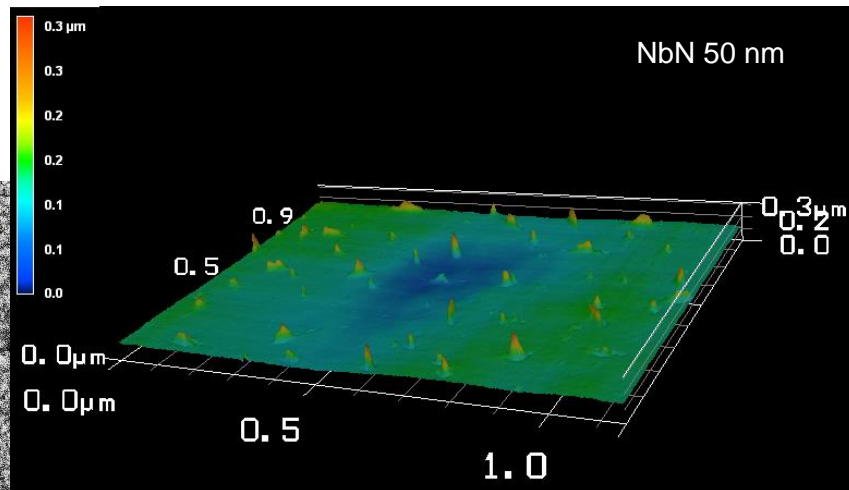
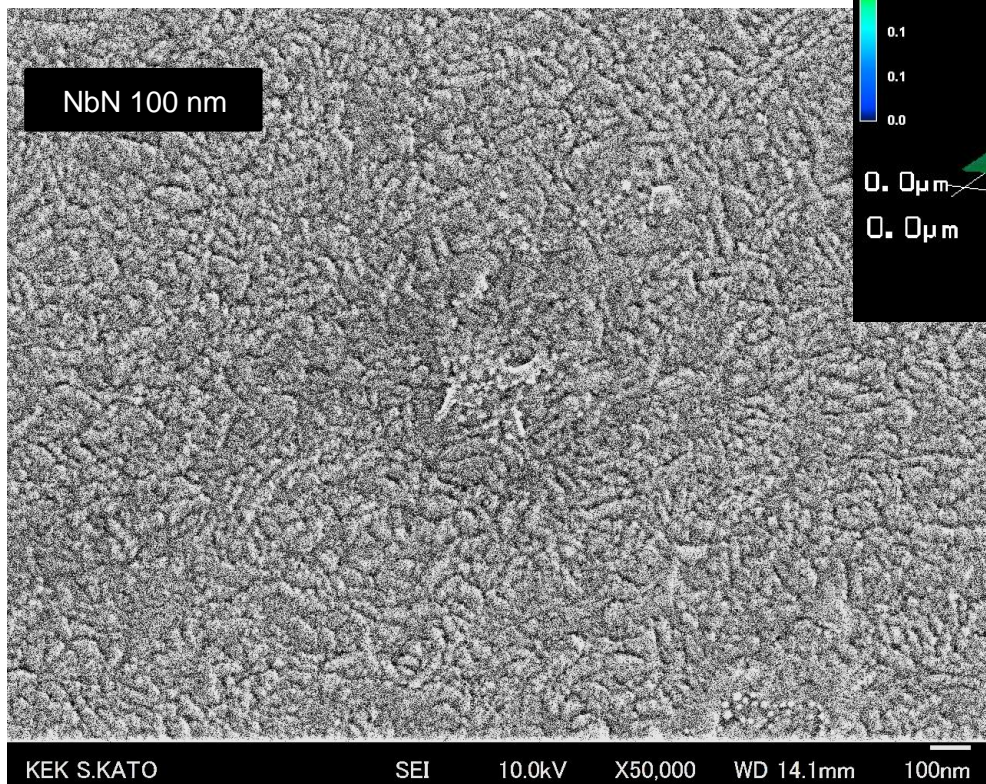
Nb (nm)	MgO (nm) Calc(actual)	NbN (nm) Calc(actual)	T <sub>c</sub> (K)
250†	14	0	8.9
250†	14	25	15.5
500	10 (10.3)	50 (65)	15*
500	10 (8.4)	75 (72)	14.1*
500	10 (9.8)	100 (94)	14*
500	10	125	14.3*
500	10 (6.7)	150 (132)	15.9*
500	10 (10.4)	200 (164)	15*

† Not same batch, deposited on the same conditions, but substrate = sapphire

\*As determined with magnetometry, see below.

## Morphology

■ Rough surface

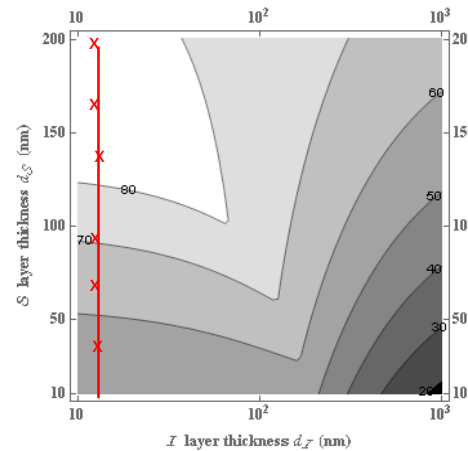
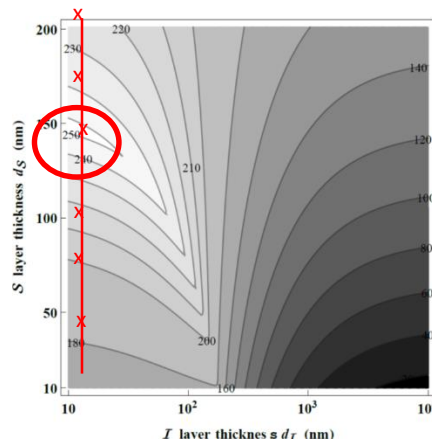


MgO needle ?  
(capping material)



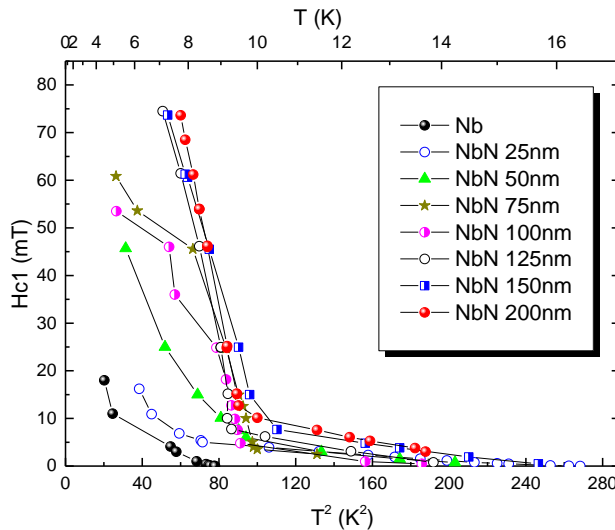
## Theoretical predictions from T. Kubo (KEK)

Ideal Nb substrate  
with  $B_{C1}=170$  mT



Nb with defects\*,  
with  $B_{C1}=50$  mT

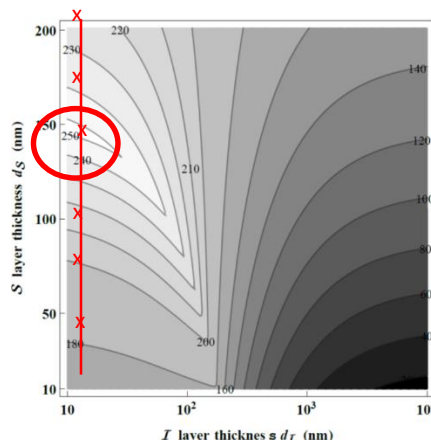
\* e.g. morphologic  
defects that allow earlier  
vortex penetration See  
SST paper cited earlier



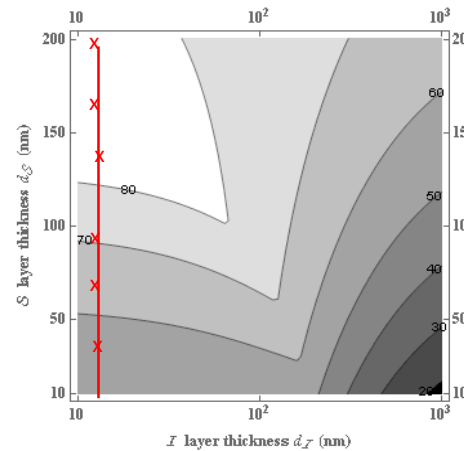
- The enhancement of the field penetration increases with thickness of NbN
- It reaches a saturation at thicknesses > 100 nm

## Theoretical predictions from T. Kubo (KEK)

Ideal Nb substrate  
with  $B_{C1}=170$  mT

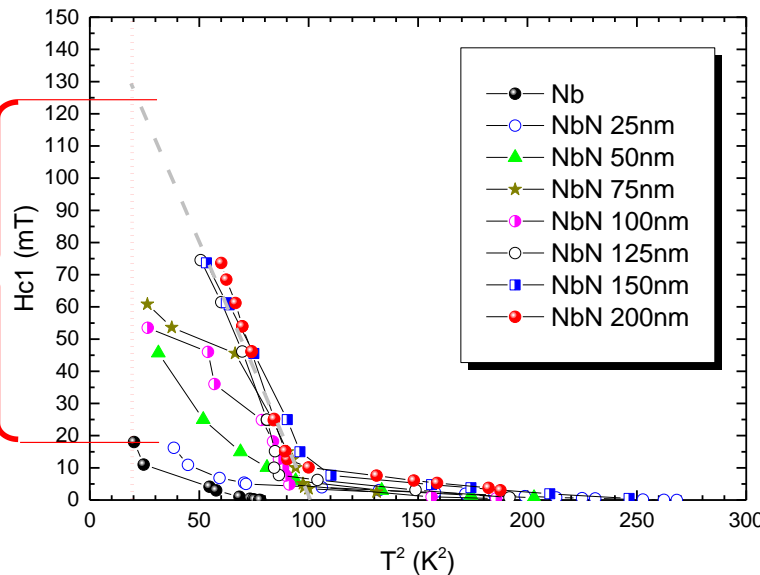


Nb with defects\*,  
with  $B_{C1}=50$  mT



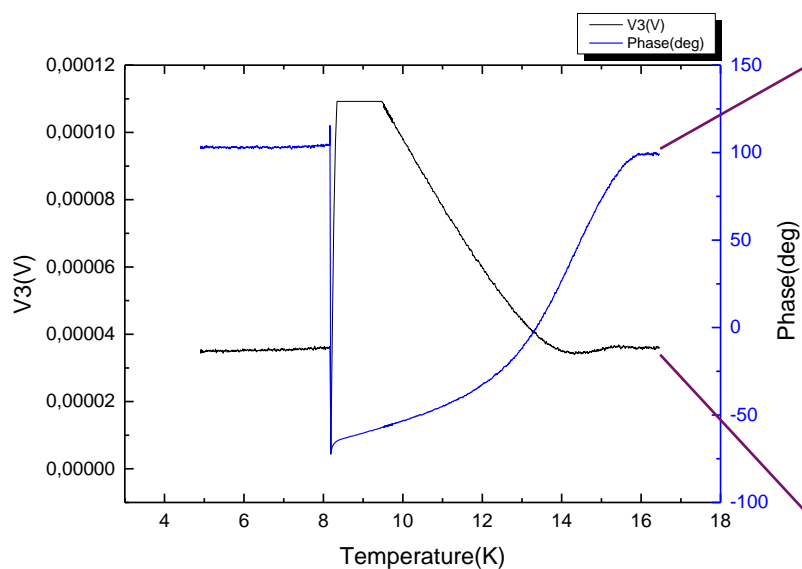
\* e.g. morphologic defects that allow earlier vortex penetration See SST paper cited earlier

@ 4.5 K  
~ + 110 mT?  
~25-30 MV/m  
ILC shape



- The enhancement of the field penetration increases with thickness of NbN
- It reaches a saturation at thicknesses > 100 nm

■ For a given  $H_{\text{appl}}$ , we observe 3  $\neq$  transition temperatures



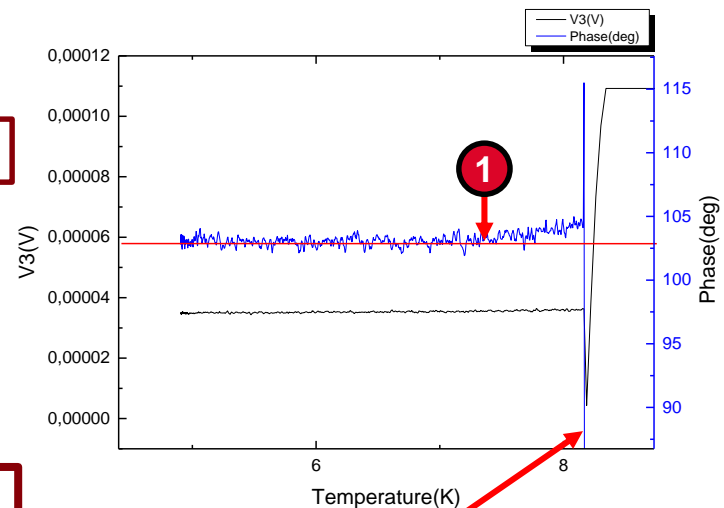
Phase signal

$T_1 \sim T_2$   
 $T_3 \gg T_2$

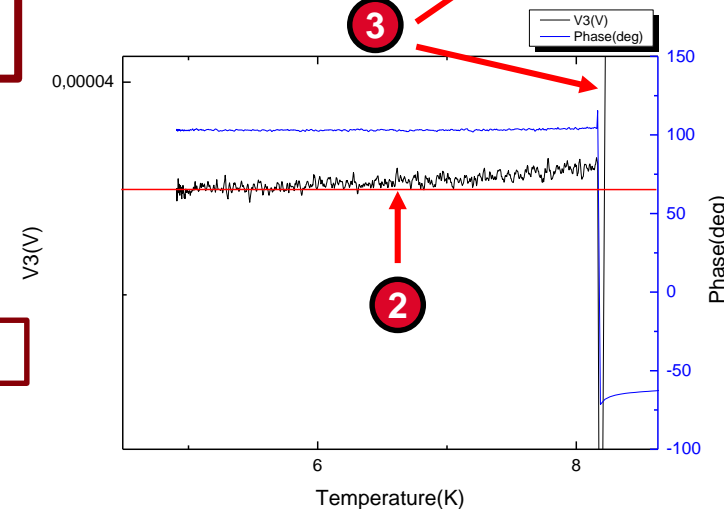
Voltage signal

■  $T_1 \sim T_2$ : within noise level

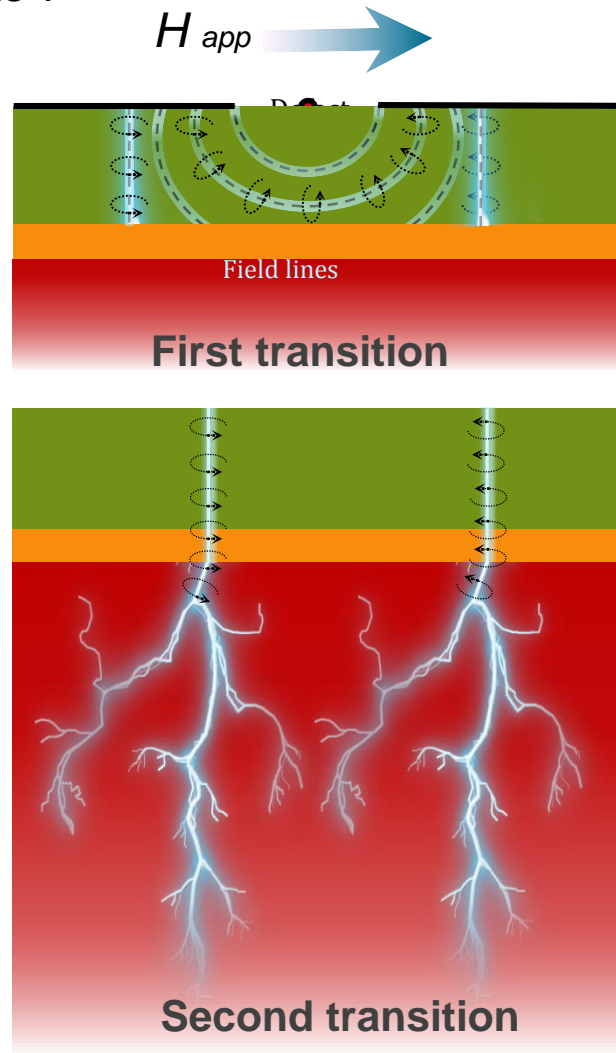
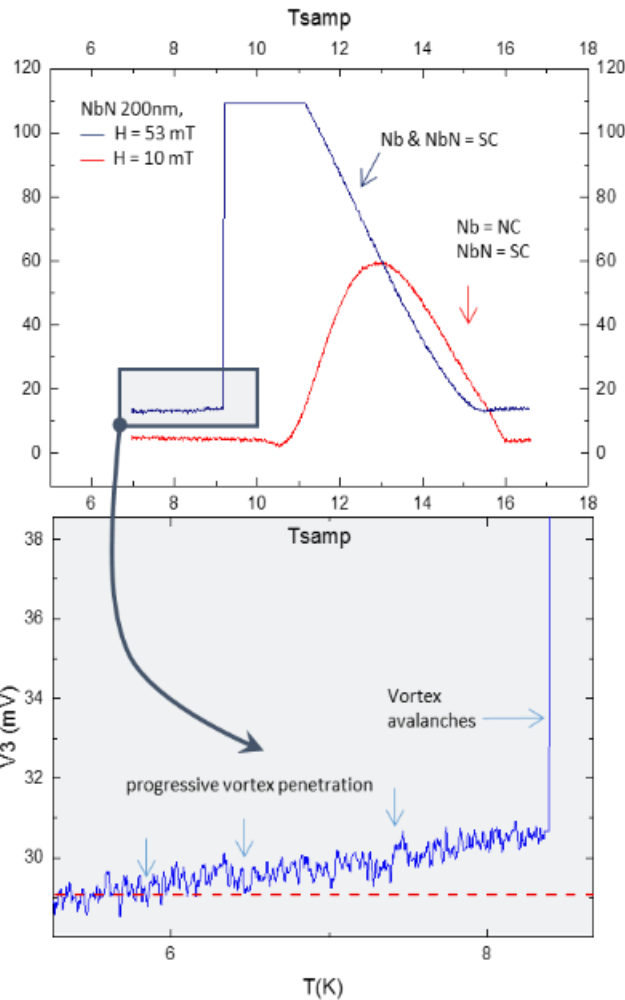
■  $T_3 \gg T_2$ : dramatic transition



3



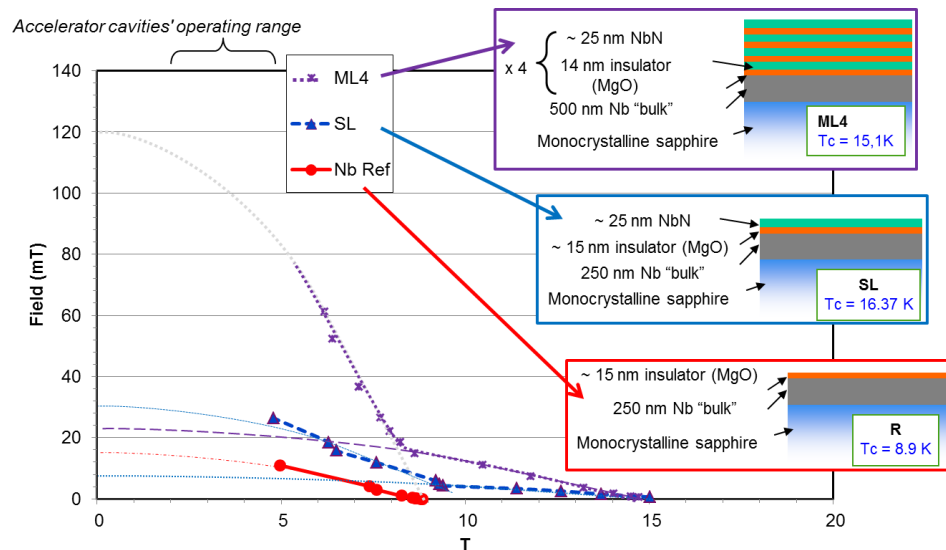
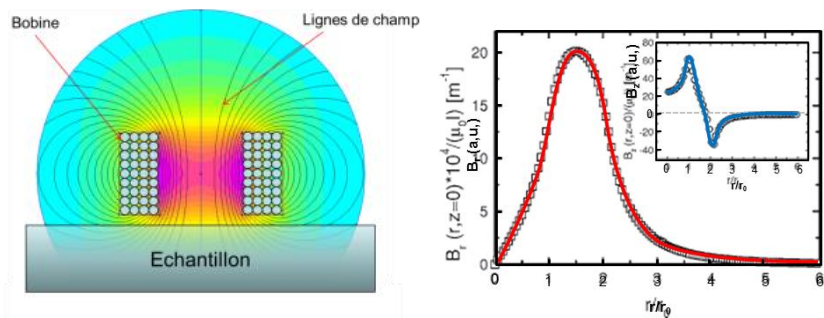
## Why do we have two transitions ?



- $H // \text{ surface} \Rightarrow \text{surface barrier}^\dagger$
- A defect locally weakens the surface barrier
- 1st transition, vortex blocked by the insulator  $\sim 100 \text{ nm} \Rightarrow \text{low dissipation}$ .
- 2nd transition, propagation of vortex avalanches ( $\sim 100 \mu\text{m}$ )  $\Rightarrow \text{high dissipation}$ .
- **Dielectric layer = efficient protection !!!**

# $H_{C1}$ ( $E_{ACC}^{MAX}$ ) AND $R_S$ ( $Q_0^{MAX}$ ) ESTIMATION

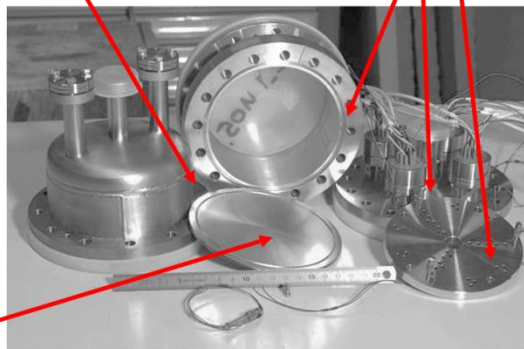
## Local magnetometry:



## RF test (collaboration IPNO)

Bulk Nb TE011 cavity body

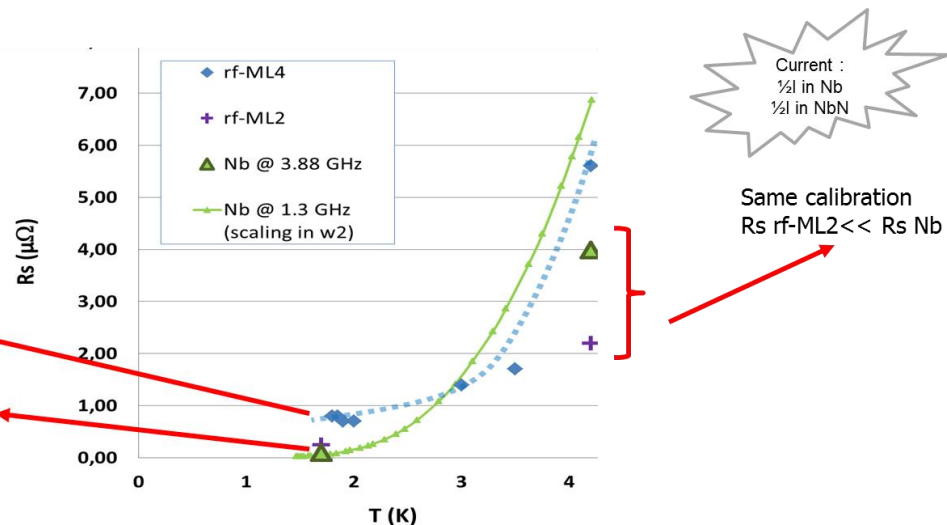
Themometric set-up



Nb disk sample 100mm

Polycrystalline Nb substrate

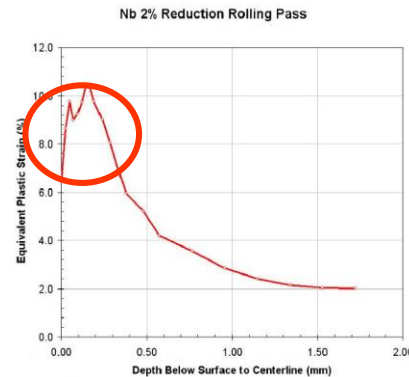
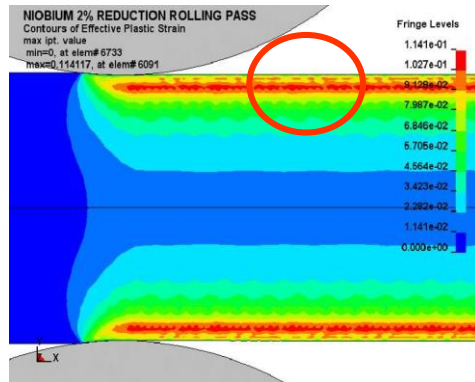
Large grain Nb substrate



**DAMMAGE LAYER**

- **High dislocation density (damage) incriminated in:**
  - Apparition of hot spots on operating cavities
  - High density of hydride precipitates
  - High sensitivity to trapped flux
- **Damage layer seems to essentially originate from rolling**
  - Surface texture resistant to recrystallization
  - Not fully eliminated after 150 $\mu$ m removal (patchy nature)

NB : in case of billet slicing damage layer is  $\neq$  and needs to be assessed



Finite element simulation of 2% reduction of 3.5 mm sheet with 1 cm diameter rolls (Courtesy Non-Linear Engineering, L.L.C.).

[R. Crook et al, Black Laboratory] &  
[http://accelconf.web.cern.ch/AccelConf/srf2009/posters/tuppo071\\_poster.pdf](http://accelconf.web.cern.ch/AccelConf/srf2009/posters/tuppo071_poster.pdf)

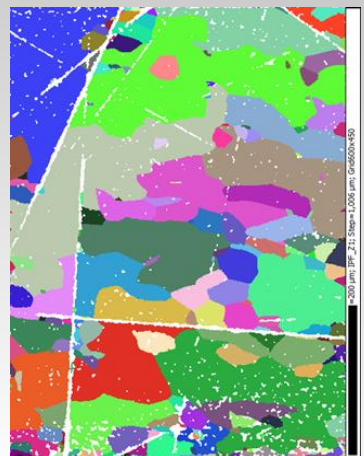
- **Postulate :**
  - Strain left by forming and welding can be easily removed by recrystallization treatment
  - => **mechanical polishing of flat sheet easy and inexpensive !!!**

*Surface of the sheet*

*New damage layer < 1µm*

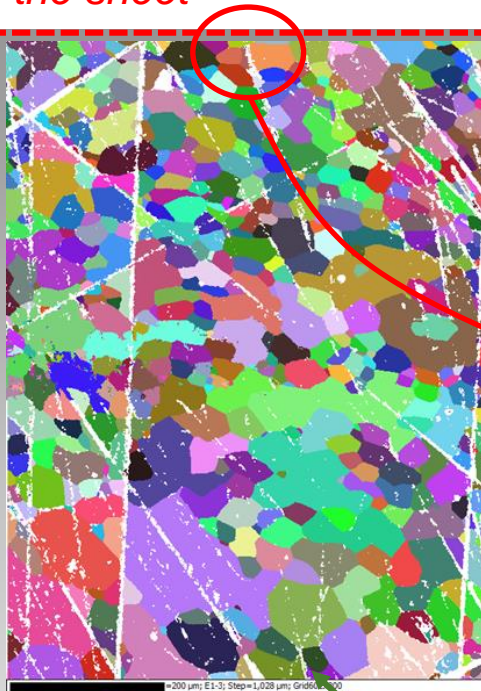


200 µm



a) As received

*Core of the sheet*

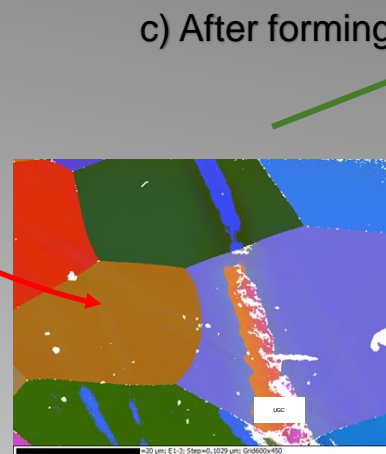


b) After 2 steps polishing

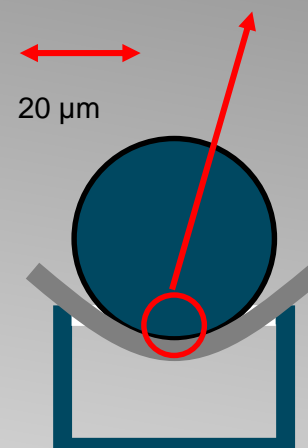
20 + 25 min  
(300 µm removed)

***Polishing on flat surface is quick and easy.***

***Mechanical chemical preparation inspired from metallographic polishing can produce damage layer ≤100 nm***



c) After forming



20 µm



- **Production already asserted to produce specification**
- **Reducing cost R&D :**
  - Today limited to only 2 directions : large grain and N infusion
  - Already promising
  - Physics not fully understood => risks
- **Longer term R&D**
  - Promising trails for improvement also exist
  - better control of the material production is required

**THANK YOU FOR YOUR ATTENTION**

# What do we measure ?



- Determination of  $H_{c1}$ 
  - Low field => one transition
  - High field => two transitions
    - » 1st transition with low dissipation
    - » 2nd transition very strong dissipation

- Why do we have two transitions ?

